

EMERGING MEMORIES TAKE OFF



COUGHLIN ASSOCIATES
San Jose, California
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SAN JOSE, CALIFORNIA**

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TABLE OF CONTENTS

	PAGE
THE AUTHORS	21
EXECUTIVE SUMMARY	23
INTRODUCTION	25
WHY EMERGING MEMORIES ARE POPULAR	29
SCALING LIMITS FOR ENTRENCHED TECHNOLOGIES	29
3D NAND FLASH TECHNOLOGIES	29
FUTURE FLASH MEMORIES	33
EMBEDDED NOR AND SRAM SCALING CHALLENGES	34
STANDALONE NAND & DRAM SCALING CONCERNS	38
TECHNICAL ADVANTAGES	38
ALTERNATIVES TO USING EMERGING MEMORIES	39
POTENTIAL COST/GB ADVANTAGES	40
THE CRUCIAL IMPORTANCE OF THE ECONOMIES OF SCALE.....	41
WHICH APPLICATIONS WANT EMERGING MEMORIES FIRST?.....	45
HOW A NEW MEMORY LAYER IMPROVES COMPUTER PERFORMANCE	46
HOW PERSISTENCE CHANGES THE MEMORY/STORAGE HIERARCHY (STORAGE CLASS MEMORIES)	46
<i>STT MRAM</i>	48
<i>ReRAM</i>	49
<i>Changes in Computer Memory Usage</i>	49
STANDARDIZING THE PERSISTENT MEMORY SOFTWARE INTERFACE	50
IN-MEMORY COMPUTING POSSIBILITIES	51
FEWER CONSTRAINTS ON MCU PROGRAMMERS	52
UNDERSTANDING BIT SELECTORS	53
RESISTIVE RAM, RERAM, RRAM, MEMRISTOR:	61
ReRAM DEVICE FUNCTION	61
SYMETRIX' CERAM.....	65
HP'S MEMRISTOR	66
STACKED RERAM ARRAYS.....	68
ReRAM CMOS INTEGRATION	69
3D STACKED RERAM CROSSPOINT SPECIFICATIONS	70
3D NAND APPROACH TO RERAM	71
ReRAM AND ARTIFICIAL INTELLIGENCE	72
CURRENT RERAM STATUS.....	73
FERROELECTRIC RAM, FERAM, FRAM	75

OPERATION OF FRAM.....	80
FRAM DEVICE CHARACTERISTICS.....	81
FERROELECTRIC FIELD EFFECT TRANSISTOR RAM (FEFET).....	83
3D FEFET FRAM	84
ANTIFERROELECTRICS AND FERROELECTRIC TUNNEL JUNCTIONS	85
THE FUTURE OF FRAM	85
PHASE CHANGE MEMORY (PCM):.....	86
OPERATION OF PCM.....	86
ADVANTAGES AND DISADVANTAGES.....	90
PCM APPLICATIONS.....	91
INTEL/MICRON 3D CROSSPOINT MEMORY	91
APPLICATIONS	93
MRAM (MAGNETIC RAM), STT MRAM (SPIN TRANSFER TORQUE MRAM) ...	96
MRAM.....	96
STT MRAM.....	99
HOW STT WORKS	102
STT MANUFACTURING.....	105
STT STRENGTHS & WEAKNESSES.....	106
SPIN-ORBIT TORQUE MRAM.....	111
MERAM, AN ALTERNATIVE SPIN MEMORY DEVICE	113
RACETRACK MEMORY	115
MRAM IN ARTIFICIAL INTELLIGENCE	116
OTHER EMERGING MEMORY TYPES	120
CARBON NANOTUBES (CNTs):.....	120
POLYMERIC FERROELECTRIC RAM (PFRAM).....	122
III-V FLOATING GATE.....	123
LITHOGRAPHY:.....	123
MULTI-PATTERNING:.....	124
FUTURE LITHOGRAPHY	125
<i>Nano-Imprinting Lithography</i>	126
EXTREME UV (EUV) TECHNOLOGY	129
3D MEMORY CIRCUIT DESIGN:	132
3D MEMORY CIRCUIT APPROACHES	133
SUMMARY OF SOLID-STATE MEMORY & STORAGE TECHNOLOGIES	134
EMERGING MEMORIES AND NEW MATERIALS	137
EMERGING MEMORY PROCESS EQUIPMENT	139
MRAM AND STT MRAM PROCESS EQUIPMENT	141
<i>Physical Vapor Deposition</i>	144
<i>Ion Beam and Plasma Etching</i>	152
<i>Photolithography (Patterning)</i>	159

<i>Other Process Equipment</i>	161
<i>Device Testing</i>	162
<i>MRAM and STT MRAM Consortia</i>	167
PHASE CHANGE MANUFACTURING EQUIPMENT	168
MEMORY IS DRIVING SEMICONDUCTOR CAPITAL SPENDING.....	169
MARKET PROJECTIONS FOR MRAM, AND 3D XPOINT MEMORY	172
MRAM SCENARIO ESTIMATES	178
3D XPOINT BANDED ESTIMATES	184
COMBINED EMERGING MEMORY ESTIMATES.....	187
ESTIMATES OF MRAM CAPITAL EQUIPMENT DEMAND	192
ION BEAM ETCHING EQUIPMENT	193
PATTERNING EQUIPMENT.....	195
MAGNETIC ANNEALING EQUIPMENT	197
PHYSICAL VAPOR DEPOSITION EQUIPMENT	199
TEST AND OTHER EQUIPMENT.....	201
SUMMARY OF MRAM EQUIPMENT DEMAND.....	203
COMPANY INFORMATION:	206
MEMORY AND APPLICATIONS COMPANIES	206
<i>4DS Memory</i>	206
<i>Adesto Technologies</i>	206
<i>Ambiq</i>	206
<i>Antaios</i>	206
<i>Arm</i>	207
<i>Avalanche Technology</i>	207
<i>BAE Systems</i>	208
<i>BeSang</i>	208
<i>CAES</i>	208
<i>CAO-SIP</i>	208
<i>CEA-Leti</i>	208
<i>Cerfe Labs</i>	208
<i>CIES</i>	209
<i>Cobham-Aeroflex</i>	209
<i>Crocus Technology</i>	209
<i>Crossbar</i>	209
<i>Cypress</i>	209
<i>Dialog Semiconductor</i>	209
<i>eVaderis</i>	210
<i>Everspin</i>	210
<i>Ferroelectric Memory Company</i>	210
<i>Fujitsu Semiconductor</i>	210
<i>GigaDevice Semiconductor, Inc.</i>	210
GLOBALFOUNDRIES.....	211
<i>Grandis</i>	211

<i>GREAT</i>	211
<i>HPE</i>	211
<i>Honeywell</i>	211
<i>IBM</i>	211
<i>imec</i>	212
<i>Institute of Microelectronics (Chinese Academy of Science)</i>	212
<i>Infineon</i>	212
<i>Integrated Device Technology (IDT)</i>	212
<i>Intel</i>	212
<i>Intermolecular</i>	213
<i>IntrinSic</i>	213
<i>Kioxia</i>	213
<i>Knowm</i>	213
<i>Lapis Semiconductor</i>	213
<i>Leti</i>	213
<i>Microchip</i>	214
<i>Micron Technology</i>	214
<i>Microsemi</i>	214
<i>NaMLab</i>	214
<i>Nantero</i>	214
<i>NEC</i>	215
<i>Numem</i>	215
<i>Nuvoton</i>	215
<i>NVE</i>	215
<i>NXP</i>	215
<i>Ovonyx</i>	216
<i>Panasonic</i>	216
<i>Qualcomm</i>	216
<i>Rambus</i>	216
<i>Ramtron</i>	216
<i>Reliance Memory</i>	216
<i>Renesas Electronics</i>	217
<i>ROHM</i>	217
<i>Samsung Semiconductor</i>	217
<i>SanDisk</i>	217
<i>Seagate Technology</i>	218
<i>SK hynix</i>	218
<i>Sony Corporation</i>	218
<i>Spin-Ion</i>	218
<i>Spin Memory</i>	219
<i>Spintec</i>	219
<i>STMicroelectronics</i>	219
<i>Symetrix</i>	220
<i>TDK</i>	220
<i>Texas Instruments</i>	220
<i>Thin Film Electronics</i>	220

<i>Unidym</i>	220
<i>Weebit Nano</i>	220
<i>Western Digital</i>	221
<i>Winbond</i>	221
SEMICONDUCTOR FAB COMPANIES.....	221
<i>DB HiTek</i>	221
<i>GLOBALFOUNDRIES</i>	221
<i>SilTerra</i>	222
<i>SMIC</i>	222
<i>TowerJazz</i>	222
<i>TSMC</i>	222
<i>UMC</i>	223
CAPITAL EQUIPMENT COMPANIES.....	223
<i>Accrettech</i>	223
<i>ANELVA</i>	223
<i>Applied Materials</i>	223
<i>ASM</i>	223
<i>ASML</i>	224
<i>Bruker</i>	224
<i>Canon</i>	224
<i>Canon-ANELVA</i>	224
<i>CAPRES A/S</i>	225
<i>EG Systems</i>	225
<i>Hitachi High Technology</i>	225
<i>Hprobe</i>	225
<i>Integral Solutions, Inc. (ISI)</i>	225
<i>Jusung Engineering</i>	225
<i>Keysight Technologies</i>	226
<i>KLA Tencor</i>	226
<i>Lake Shore</i>	226
<i>Lam Research</i>	226
<i>Leuven Instruments</i>	226
<i>MagOasis</i>	227
<i>MicroSense</i>	227
<i>Nanomagnetics Instruments</i>	227
<i>Nanometrics</i>	227
<i>Neoark</i>	227
<i>Nikon</i>	227
<i>Onto Innovation</i>	227
<i>Oxford Instruments</i>	228
<i>Plasma Therm</i>	228
<i>SHB</i>	228
<i>Singulus Technologies</i>	228
<i>Smart Tip</i>	228
<i>Tokyo Electron</i>	228
<i>Tokyo Seimitsu</i>	228

<i>Ulvac</i>	228
<i>Veeco</i>	229
FURTHER READING	230

LIST OF TABLES

TABLE	PAGE
TABLE 1. DRAM AND SLC NAND DIE SIZES	41
TABLE 2. COMPARISON OF VARIOUS SOLID STATE MEMORY TECHNOLOGIES.....	48
TABLE 3. SUMMARY OF EMERGING MEMORY TECHNOLOGIES.....	136
TABLE 4. SOME MRAM PROCESS EQUIPMENT VENDORS	144
TABLE 5. TOKYO ELECTRON MAGNETIC ANNEALING PRODUCT LINE-UP	161
TABLE 6. 2020 VERSUS 2019 EQUIPMENT SPENDING BY REGION (\$B).	170
TABLE 7. STANDALONE MEMORY PRICES, 2019-2031 (\$/GB)	173
TABLE 8. STANDALONE MEMORY ANNUAL BASELINE PETABYTE SHIPMENTS, 2019 THROUGH 2031	175
TABLE 9. ASSUMPTIONS FOR BASELINE STANDALONE MRAM MODEL	176
TABLE 10. STANDALONE MEMORY ANNUAL BASELINE REVENUE, 2020-2030 (\$M).....	177
TABLE 11. THREE SCENERIOS FOR STANDALONE MRAM WAFER CONSUMPTION, 2020-2031	179
TABLE 12. THREE SCENARIOS FOR EMBEDDED MRAM ANNUAL WAFER CONSUMPTION, 2020-2031	180
TABLE 13. THREE SCENARIOS FOR COMBINED MRAM ANNUAL WAFER CONSUMPTION, 2020-2031	182
TABLE 14. THREE SCENARIOS COMBINED MRAM PRODUCTION, 2020-2031 (PETABYTES)	183
TABLE 15. THREE SCENARIOS FOR COMBINED MRAM REVENUES, 2020-2031 (\$M).....	184
TABLE 16. THREE SCENARIOS FOR 3D XPOINT PETABYTE PRODUCTION, 2020-2031	185

TABLE 17. THREE SCENARRIOS FOR 3D XPOINT REVENUES, 2020-2031	186
TABLE 18. COMBINED MRAM AND 3D XPOINT PRODUCTION, HIGH ESTIMATE, 2020-2031 (PETABYTES)	188
TABLE 19. COMBINED MRAM AND 3D XPOINT PRODUCTION, BASELINE ESTIMATE, 2020-2031 (PETABYTES)	188
TABLE 20. COMBINED MRAM AND 3D XPOINT PRODUCTION, LOW ESTIMATE, 2020-2031 (PETABYTES)	189
TABLE 21. COMBINED MRAM AND 3D XPOINT REVENUES, HIGH ESTIMATE, 2020-2031 (\$M)	190
TABLE 22. COMBINED MRAM AND 3D XPOINT REVENUES BASELINE ESTIMATE, 2020-2031 (\$M)	190
TABLE 23. COMBINED MRAM AND 3D XPOINT REVENUES LOW ESTIMATE, 2020-2031 (\$M)	191
TABLE 24. MRAM ION BEAM ETCHING EQUIPMENT BASELINE UNIT SHIPMENT ESTIMATES, 2020-2031	193
TABLE 25. MRAM ION BEAM ETCHING EQUIPMENT BASELINE SPENDING ESTIMATES, 2020-2031	194
TABLE 26. MRAM PATTERNING EQUIPMENT BASELINE UNIT SHIPMENT ESTIMATES, 2020-2031	195
TABLE 27. MRAM PATTERNING EQUIPMENT BASELINE SPENDING ESTIMATES, 2020-2031 (\$M)	196
TABLE 28. MRAM MAGNETIC ANNEALING EQUIPMENT BASELINE UNIT SHIPMENT ESTIMATES 2020-2031	197
TABLE 29. MRAM MAGNETIC ANNEALING EQUIPMENT BASELINE SPENDING ESTIMATES 2020-2031	197
TABLE 30. MRAM PHYSICAL VAPOR DEPOSITION EQUIPMENT BASELINE UNIT SHIPMENT ESTIMATES, 2020-2031	199
TABLE 31. MRAM PHYSICAL VAPOR DEPOSITION EQUIPMENT BASELINE SPENDING ESTIMATES, 2020-2031 (\$M)	200
TABLE 32. MRAM TEST AND OTHER EQUIPMENT BASELINE UNIT SHIPMENT ESTIMATES, 2020-2031	201
TABLE 33. MRAM TEST AND OTHER EQUIPMENT PRICE ESTIMATES, 2020-2031 (\$M)	201

TABLE 34. MRAM TEST AND OTHER EQUIPMENT BASELINE SPENDING ESTIMATES, 2020-2031 (\$M) 202

TABLE 35. MRAM COMBINED EQUIPMENT BASELINE UNIT SHIPMENT ESTIMATES, 2020-2031..... 204

TABLE 36. MRAM COMBINED EQUIPMENT BASELINE SPENDING, 2020-2031 (\$M)..... 204

LIST OF FIGURES

FIGURE	PAGE
FIGURE 1. MEMORY DENSITY AND POWER REQUIREMENTS BY APPLICATION CATEGORY	25
FIGURE 2. SOLID STATE MEMORY/STORAGE TECHNOLOGIES	26
FIGURE 3. 3D NAND FLASH MEMORY TOPOLOGY.....	30
FIGURE 4. TOSHIBA'S BICS AND SAMSUNG'S TCAT 3D NAND STRUCTURES	31
FIGURE 5. COST OF TRANSITION FROM ONE NAND MANUFACTURING PROCESS TO THE NEXT	32
FIGURE 6. PROJECTED NAND FLASH CHIP TECHNOLOGY ROADMAP ..	33
FIGURE 7. SRAM CELL SIZES SHRINK MORE SLOWLY THAN PROCESSES	35
FIGURE 8. HISTORICALLY, SRAM CACHES SCALED IN PROPORTION TO PROCESSOR LOGIC	36
FIGURE 9. SRAM IN FUTURE PROCESSES WILL SCALE MORE SLOWLY THAN PROCESSOR LOGIC	36
FIGURE 10. SRAM CELL SIZE VS. PROCESS FOR INTEL, SAMSUNG, AND TSMC	37
FIGURE 11. NAND FLASH PRICES CROSSED BELOW DRAM IN 2004	42
FIGURE 12. 2004 NAND GIGABYTE SHIPMENTS REACHED 1/3RD THAT OF DRAM	43
FIGURE 13. ESTIMATED INTEL 3D XPOINT QUARTERLY LOSSES	44
FIGURE 14. COMPARISON OF MEMORY AND STORAGE TECHNOLOGIES BY PRICE PER GIGABYTE AND PERFORMANCE.....	46
FIGURE 15. EVERSPIN 1 GB STT MRAM CHIP	49
FIGURE 16. PROGRESSION OF STORAGE TECHNOLOGIES WITH NONVOLATILE SOLID-STATE STORAGE	50

FIGURE 17. CONTRIBUTORS TO NONVOLATILE SOLID-STATE STORAGE LATENCY WITH LEGACY AND CURRENT SOLID-STATE NONVOLATILE TECHNOLOGIES.....	51
FIGURE 18. RERAM SYSTEM ON CHIP	52
FIGURE 19. BIT SELECTORS - 3-TERMINAL (LEFT) 2-TERMINAL (RIGHT)	54
FIGURE 20. OVERHEAD VIEW OF A SIMPLE CROSSPOINT ARRAY	54
FIGURE 21. READING WHEN ONE BIT IS IN A LOW-RESISTANCE STATE	55
FIGURE 22. SNEAK PATHS OCCUR WHEN MULTIPLE BITS ARE IN A LOW RESISTANCE STATE	55
FIGURE 23. SPACE PENALTY OF A 3-TERMINAL SELECTOR	57
FIGURE 24. BIDIRECTIONAL DIODE SELECTOR.....	58
FIGURE 25. A 1TNR SELECTOR CONFIGURATION	59
FIGURE 26. 3D CROSSPOINT ARRAY STACKING	59
FIGURE 27. STACKED CROSSPOINT MEMORY ARRAY	60
FIGURE 28. RERAM FILAMENT CELL CONDUCTION AND SWITCHING	62
FIGURE 29. RERAM SCALING.....	63
FIGURE 30. RERAM RESISTANCE SCALING.....	63
FIGURE 31. TAOX RERAM DEVICE	64
FIGURE 32. CURRENT LEVELS AND VOLTAGES FOR RERAM SWITCHING.....	65
FIGURE 33. COMPARING CERAM CELL STRUCTURE TO RERAM	66
FIGURE 34. WHERE THE MEMRISTOR FITS IN THE WORLD OF PASSIVE CMONENTS	67
FIGURE 35. RERAM STACKED CROSSPOINT ARRAY	68
FIGURE 36. RERAM CMOS INTEGRATION	69
FIGURE 37. TWO-MASK RERAM ELEMENT IN TUNGSTEN VIAS.....	70
FIGURE 38. RERAM MEMORY BANK	71
FIGURE 39. 3D RERAM STRUCTURE/PROCESS.....	71

FIGURE 40. A SIMPLIFIED VIEW OF A NEURAL NETWORK.....	72
FIGURE 41. EARLY FERROELECTRIC MEMORY - 1955 BELL LABS 256-BIT DEVICE.....	75
FIGURE 42. HYSTERESIS CURVE OF FERROELECTRIC MEMORY	76
FIGURE 43. PUBLICATION COUNT FOR FEFET RESEARCH PAPERS	78
FIGURE 44. AMORPHOUS, CRYSTALLINE, AND FERROELECTRIC HAFNIUM OXIDE	78
FIGURE 45. PZT AND HFO CAPACITORS, SHOWING TYPICAL DIMENSIONS	79
FIGURE 46. FRAM PEROVSKITE DISPLACEMENT	80
FIGURE 47. MEMORY PROPERTIES OF FERROELECTRIC HAFNIUM OXIDE AS DERIVED FROM EXPERIMENTS AND EXPECTED MATERIAL LIMITS	81
FIGURE 48. FRAM PLANAR CELL STRUCTURE	82
FIGURE 49. FEFET TRANSISTOR	83
FIGURE 50. 3D HAFNIUM OXIDE FRAM BUILT USING 3D NAND TECHNIQUES	84
FIGURE 51. CROSSPOINT MEMORY USING PCM CELLS	87
FIGURE 52. CHARACTERISTICS OF THE READ, WRITE AND ERASE CYCLE FOR PCM MATERIALS.....	88
FIGURE 53. PCM MEMORY CELL	88
FIGURE 54. CROSS SECTION OF PCM CELL.....	89
FIGURE 55. STMICROELECTRONICS' TRANSISTOR-SELECTED PCM CELL	89
FIGURE 56. INTEL'S VIEW OF THE MEMORY-STORAGE HIERARCHY	94
FIGURE 57. REDIS VIRTUAL MACHINE COUNT VS. MEMORY SIZE	95
FIGURE 58. BASIC CELL DIAGRAM FOR FIELD SWITCHED MRAM	96
FIGURE 59. FIELD SWITCHED ARRAY MRAM ARCHITECTURE	97
FIGURE 60. GLOBALFOUNDRIES ROADMAP FOR EMBEDDED MRAM ..	100
FIGURE 61. TSMC'S EMBEDDED MRAM/RRAM PLANS.....	102

FIGURE 62. PARALLEL TO ANTIPARALLEL SWITCHING.....	104
FIGURE 63. SPIN TRANSFER TORQUE OPERATION	104
FIGURE 64. IN PLANE AND PERPENDICULAR MAGNETIC TUNNEL CELLS	104
FIGURE 65. STT MRAM CELL STRUCTURE.....	105
FIGURE 66. EVERS PIN STT MRAM DEVICE.....	106
FIGURE 67. STT MRAM CURRENT OPERATION	107
FIGURE 68. MULTI-BIT MRAM CELL READ OUT	108
FIGURE 69. A COMPARISON OF DRAM, NAND FLASH AND STT MRAM	109
FIGURE 70. STT MRAM CROSS SECTION	109
FIGURE 71. BIT DIMENSIONS OF IDEAL MRAM, DRAM, PLANAR NAND FLASH AND HDD.....	110
FIGURE 72. STT MRAM EMBEDDED MEMORY	111
FIGURE 73. STT-MRAM TO SOT-MRAM	112
FIGURE 74. EXAMPLE MERAM DEVICE STRUCTURE.....	113
FIGURE 75. MERAM STACK.....	114
FIGURE 76. IBM'S RACETRACK MEMORY - CONCEPTUAL DIAGRAM	115
FIGURE 77. LABORATORY EMBODIMENT OF IBM'S RACETRACK MEMORY	116
FIGURE 78. GYRFALCON AI ACCELERATOR WITH MRAM.....	117
FIGURE 79. NUMEN DNN DEVICE WITH MRAM FOR SPACE APPLICATIONS	118
FIGURE 80. AMBIQ APOLLO IOT SOC	119
FIGURE 81. SONY EMRAM BUFFER MEMORY FOR CIS	119
FIGURE 82. CNT FABRIC.....	121
FIGURE 83. PFRAM 3-LAYER POLYMERIC MEMORY	122
FIGURE 84. ORIGINAL SINGLE-PATTERNED FEATURES.....	124
FIGURE 85. CLAD THE SIDES OF THE ORIGINAL PATTERN.....	125

FIGURE 86. REMOVE THE ORIGINAL PATTERN. THE REMAINING CLADDING IS A DOUBLED PATTERN.....	125
FIGURE 87. CLAD THE SIDES OF THE DOUBLED PATTERN	125
FIGURE 88. REMOVE THE DOUBLED PATTERN. THE REMAINING CLADDING IS THE QUADRUPLED PATTERN.....	125
FIGURE 89. NANOIMPRINT PROCESS	127
FIGURE 90. NANOIMPRINT DEPRESSIONS.....	128
FIGURE 91. FLUID DISPENSE PROCESS.....	128
FIGURE 92. LIGHT SPECTRUM	129
FIGURE 93. EUV SCANNING LITHOGRAPHIC EXPOSURE SYSTEM.....	130
FIGURE 94. BIT DENSITY OF LARGEST MEMORIES PRESENTED AT IEEE RESEARCH CONFERENCES, 2001-2019.....	135
FIGURE 95. FUTURE MEMORY/STORAGE HIERARCHY	137
FIGURE 96. EXAMPLE ELEMENTS TO ENABLE NEW MEMORIES.....	138
FIGURE 97. COMPARISON OF MULTIPLE EMERGING MEMORY CELL STRUCTURES.....	139
FIGURE 98. MRAM MEMORY CELL	141
FIGURE 99. CROSS-SECTION OF AN MRAM DEVICE SHOWING DETAILS OF THE CMOS SUBSTRATE AND MAGNETIC LAYERS FABRICATED ON TOP OF THE SUBSTRATE	142
FIGURE 100. MRAM MANUFACTURING PROCESS FLOW	143
FIGURE 101. KEY MRAM PROCESS EQUIPMENT.....	143
FIGURE 102. APPLIED MATERIALS CMP SYSTEM.....	146
FIGURE 103. APPLIED MATERIALS ENDURA PLATFORM	146
FIGURE 104. CANON ANELVA EC7800 PVD EQUIPMENT	147
FIGURE 105. CANON ANELVA NC7900 PVD EQUIPMENT	148
FIGURE 106. SINGULUS TIMARIS II PVD CLUSTER TOOL PLATFORM... 	148
FIGURE 107. SINGULUS PVD CLUSTER TOOL PLATFORMS.....	149

FIGURE 108. TOKYO ELECTRON EXIM PVD CLUSTER TOOL PLATFORM	150
FIGURE 109. ULVAC MAGEST S200 MULTILAYER THIN FILM DEPOSITION SYSTEM	151
FIGURE 110. VEECO NEXUS IBD ION BEAM DEPOSITION SYSTEM	151
FIGURE 111. A THREE GRID ION BEAM EXTRACTION SYSTEM	152
FIGURE 112. SCHEMATIC OF MTJ ETCHING PROCESS	153
FIGURE 113. APPLIED MATERIALS CENTURA TOOL	153
FIGURE 114. CANON ANELVA NC8000 ION BEAM ETCH MACHINE.....	154
FIGURE 115. HITACHI HIGH TECHNOLOGY E-600/8000 NONVOLATILE ETCH SYSTEM	155
FIGURE 116. LAM RESEARCH KIYO ION BEAM ETCHING CHAMBER	156
FIGURE 117. OXFORD INSTRUMENTS IONFAB 300 IBE SYSTEM	156
FIGURE 118. PLASMA THERM PINNACLE ION BEAM ETCH AND DEPOSITION SYSTEM	157
FIGURE 119. ULVAC ULHITE NE-7800H NON-VOLATILE MATERIAL ETCHING TOOL	158
FIGURE 120. VEECO NEXUS IBE-420I ION BEAM ETCHING SYSTEM	158
FIGURE 121. ASML DEEP UV PHOTOLITHOGRAPHY TOOL	159
FIGURE 122. NIKON PHOTOLITHOGRAPHIC PRODUCT LINES	160
FIGURE 123. CANON LITHOGRAPHIC I-LINE STEPPER PRODUCT LINE	160
FIGURE 124. TOKYO ELECTRON MRT300 MAGNETIC ANNEALING TOOL	161
FIGURE 125. ISI WLA 3000 WAFER LEVEL QUASI-STATIC TESTER	162
FIGURE 126. HPROBE 3D HIGH MAGNETIC FIELD WAFER PROBE.....	164
FIGURE 127. KEYSIGHT TECHNOLOGY NX5730A MRAM TEST PLATFORM	164
FIGURE 128. MICROSENSE (KLA/TENCOR) POLAR KERR SYSTEM FOR PERPENDICULAR STT MRAM.....	165
FIGURE 129. AFM EQUIPMENT	166

FIGURE 130. APPLIED MATERIALS ENDURA IMPULSE FOR PCM AND RERAM	168
FIGURE 131. SEMI'S WAFER FAB EQUIPMENT SPENDING HISTORY AND FORECAST	169
FIGURE 132. EQUIPMENT SPENDING BY REGION	170
FIGURE 133. VOLUME SEMICONDUCTOR FABRS BY REGION	171
FIGURE 134. PROFITABILITY OF NAND FLASH MANUFACTURERS	172
FIGURE 135. CHART OF BASELINE \$/GB FOR STANDALONE MEMORY TECHNOLOGIES FROM 2018 THROUGH 2030	174
FIGURE 136. STANDALONE MEMORY ANNUAL BASELINE PETABYTE SHIPMENTS, 2019-2031	175
FIGURE 137. STANDALONE MEMORY BASELINE ANNUAL REVENUE, 2019-2030 (\$M)	178
FIGURE 138. THREE SCENARIOS FOR STANDALONE MRAM WAFER CONSUMPTION, 2020-2031	180
FIGURE 139. THREE SCENARIOS FOR EMBEDDED MRAM ANNUAL WAFER CONSUMPTION , 2020-2031	181
FIGURE 140. THREE SECEARIOS FOR COMBINED MRAM ANNUAL WAFER CONSUMPTION, 2020-2031	182
FIGURE 141. THREE SCENARIOS FOR COMBINED MRAM PRODUCTION, 2020-2031 (PETABYTES)	183
FIGURE 142. THREE SCENARIOS FOR COMBINED MRAM REVENUES, 2020-2031 (\$B)	184
FIGURE 143. THREE SCENARIOS FOR 3D XPOINT PETABYTE PRODUCTION, 2020-2031	186
FIGURE 144. THREE SCENARIOS FOR 3D XPOINT REVENUES, 2020-2031	187
FIGURE 145. THREE SCENARIOS OF COMBINED MRAM AND 3D XPOINT EXABYTE PRODUCTION, 2020-2031	189
FIGURE 146. THREE SCENARIOS OF COMBINED MRAM AND 3D XPOINT REVENUES, 2020-2031 (\$B)	191
FIGURE 147. CAPITAL EQUIPMENT ESTIMATE PROCESS FLOW	192

FIGURE 148. THREE SCENARIOS OF MRAM ION BEAM ETCHING EQUIPMENT SPENDING, 2020-2031	194
FIGURE 149. THREE SCENARIOS OF MRAM PATTERNING EQUIPMENT SPENDING, 2020-2031 (\$M).....	196
FIGURE 150. THREE SCENARIOS OF MRAM MAGNETIC ANNEALING EQUIPMENT SPENDING 2020-2031	198
FIGURE 151. THREE SCENARIOS OF MRAM PHYSICAL DEPOSITION EQUIPMENT SPENDING, 2020-2030 (\$M).....	200
FIGURE 152. MRAM COMBINED TEST AND OTHER EQUIPMENT BASELINE SPENDING, 2020-2031 (\$M).....	202
FIGURE 153. THREE SCENARIOS OF MRAM TEST AND OTHER EQUIPMENT SPENDING, 2020-2031 (\$M).....	203
FIGURE 154. MRAM COMBINED BASELINE EQUIPMENT SPENDING ESTIMATES, 2020-2031 (\$M)	205
FIGURE 155. THREE SCENARIOS FOR MRAM COMBINED EQUIPMENT SPENDING, 2020-2031 (\$M).....	205

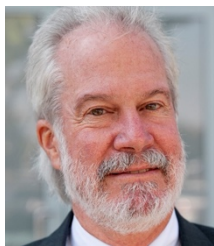
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EXECUTIVE SUMMARY

Current memory technologies including flash memory (NAND and NOR), DRAM and SRAM are facing potential technology limits to their continued improvement. As a result, there are intense efforts to develop new memory technologies. Most of these new technologies are nonvolatile memories and can be used for long-term storage or to provide a memory that retains information when powered down. This offers advantages for battery and ambient powered devices and also for energy savings in data centers.

The memories addressed in this report include PCM, ReRAM, FRAM, Toggle MRAM, STT MRAM and a variety of less mainstream technologies such as carbon nanotubes. Based upon the level of current development and the characteristics of these technologies, resistive RAM (ReRAM) may be a potential replacement for flash memory. However, NAND flash memory has several generations of technologies that will be implemented before a replacement is required. Thus, this transition will not fully occur until the next decade at the earliest.

Micron and Intel's introduction of 3D XPoint memory, a technology that has high endurance, performance much better than NAND, although somewhat slower than DRAM, and higher density than DRAM, could impact the need for DRAM. Intel introduced NVMe SSDs with its Optane technology (using 3D XPoint) in 2017 and began to ship NVDIMM Optane products in 2019, in support of its newest generation of server processors, the Second-Generation Intel Xeon Scalable Processors. 3D XPoint uses a type of phase change technology.

Magnetic RAM (MRAM) and spin transfer torque RAM (STT MRAM) will start to replace some NOR flash, SRAM and possibly DRAM within the next few years and probably before ReRAM replaces NAND flash memory. The rate of development in STT MRAM and MRAM capabilities will gradually result in lower prices, and the attractiveness of replacing volatile memory with high speed and high endurance nonvolatile memory make these technologies very competitive, assuming that their volume increases to reduce production costs (and thus purchase prices).

Ferroelectric RAM (FRAM) and some ReRAM technologies have some niche applications and with the use of HfO FRAM the number of niche markets available for FRAM could increase.

Moving to a nonvolatile solid-state main memory and cache memory will reduce power usage directly as well as enable new power saving modes, provide faster recovery from power off and enable more stable computer architectures that retain their state even when power is off. Eventually spintronic technology, that uses spin rather than current for logic functions, could be used to make future microprocessors. Spin-based logic could enable very efficient in-memory computing. Several emerging memory technologies are also being used in neuromorphic computing experiments.

The use of a nonvolatile technology as an embedded memory combined with CMOS logic has great importance in the electronics industry. NOR flash reached its scaling limit at 28nm, and soon will be replaced with one of these new technologies. As a replacement for a multi-transistor SRAM, STT MRAM could dramatically reduce the number of memory transistors and thus provide a low cost, higher-density solution.

A number of enterprise and consumer devices use MRAM, based on field switching, to act as an embedded cache memory, and this trend will continue.

The availability of STT MRAM has accelerated this trend. Because of the compatibility of MRAM and STT-RAM processes with conventional CMOS processes, these memories can be built directly on top of CMOS logic wafers. Flash memory doesn't have the same compatibility with conventional CMOS. The power savings of nonvolatile and simpler MRAM and STT MRAM when compared with SRAM is significant. As MRAM \$/GB costs approach those of SRAM, this replacement could cause significant market expansion.

We project that 3D XPoint memory, with significant gigabyte shipments in 2020-2021, and with its important price advantage versus DRAM, will grow to a baseline level of 552EB (exabytes) of shipping capacity by 2031. 3D XPoint baseline revenues are projected to reach \$20.6B by 2031.

It is projected that total MRAM and STT MRAM baseline annual shipping capacity will rise from an estimated 40TB in 2020 to 991PB in 2031. Total MRAM and STT-RAM baseline revenues are expected to increase from \$43M in 2020 to about \$24B by 2031. Much of this revenue gain will be at the expense of SRAM, NOR flash and some DRAM, although STT-RAM is developing its own special place in the pantheon of shipping memory technologies.

The demand for MRAM and STT-MRAM will drive demand for capital equipment to manufacture these devices. While MRAM and STT-MRAM can be built on standard CMOS circuits supplied by large semiconductor fabricators, MRAM and STT MRAM do require specialized fabrication equipment for the MRAM layers that is similar to or the same as that used in manufacturing the magnetic read sensors in hard disk drives.

The increasing demand for nonvolatile memory based upon MRAM and STT MRAM will cause total manufacturing equipment revenue used for making the MRAM devices to rise from an estimated \$9.9M in 2020 to between \$208M to \$2.4B by 2031 with a baseline projected spending of \$1.2B.



OBJECTIVE ANALYSIS

Semiconductor Market Research

Coughlin Associates

Data Storage Consulting

EMERGING MEMORIES TAKE OFF

Available July, 2021

This report, jointly produced by Objective Analysis and Coughlin Associates, provides an exhaustive look at emerging memory technologies and their interaction with standard memories, both as discrete devices and in embedded applications (the memories within logic chips like ASICs and MCUs). The report provides a well of technical information, market dynamics, forecasts, and competitive analyses of the leading companies. Forecasts show how the markets will grow not only for the technologies themselves, but also for the capital equipment used to produce them. Read this to understand the competitive landscape and market drivers for these new memories, and to learn how to profit from tomorrow's market.

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